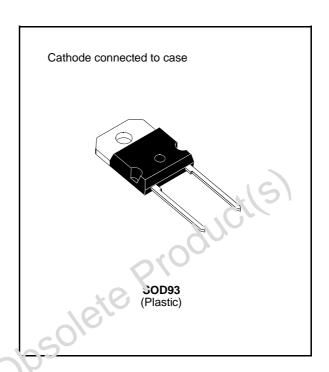


FAST RECOVERY RECTIFIER DIODE

- VERY HIGH REVERSE VOLTAGE CAPABILITY
- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING



SUITABLE APPLICATIONS

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parame. er	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1000	V
V_{RSM}	Non Repetitive Peak Reverse Voltage	1000	V
I _{FRM}	Repetive Peak To ward Current	375	Α
I _{F (RMS)}	RMS Forv and Current	70	Α
I _{F (AV)}	A\ erage Forward Current	30	Α
I _{F(M}	Surge non Repetitive Forward Current	200	А
Р	Power Dissipation	60	W
T _{stg} T _j	Storage and Junction Temperature Range	- 40 to +150 - 40 to +150	°C

THERMAL RESISTANCE

ĺ	Symbol	Parameter	Value	Unit
	R _{th (j - c)}	Junction-case	1	°C/W

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Synbol		Min.	Тур.	Max.	Unit	
I _R	T _j = 25°C	$V_R = V_{RRM}$			100	μΑ
	T _j = 100°C				5	mA
V _F	T _j = 25°C	I _F = 30A			1.9	V
	T _j = 100°C				1.8	

RECOVERY CHARACTERISTICS

Symbol		Min.	Тур.	Max.	Unit			
t _{rr}	T _j = 25°C	I _F = 1A	$di_F/dt = -15A/\mu s$	$V_R = 30V$			165	ns
		I _F = 0.5A	I _R = 1A	$I_{rr} = 0.25A$			70	

TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol	Test Conditions			Тур.	Max.	Unit
t _{IRM}	$di_F/dt = - 120A/\mu s$	V _{CC} = 200 V I _F = 30A			200	ns
	$di_F/dt = -240A/\mu s$	$L_p \le 0.05 \mu H$ $T_j = 100^{\circ} C$ See figure 11		120		
I _{RM}	$di_F/dt = -120A/\mu s$				19.5	Α
	$di_F/dt = -240A/\mu s$			22		

TURN-OFF OVERVOLTAGE COEFFICIENT (With Series Inductance)

Symbol		Test Conditions			Тур.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$	T _j = 100°C di _F /dt = - 30A/μs	$V_{CC} = 200V$ $L_p = 5\mu H$	I _F = I _{F (AV)} See figure 12			4.5	

To evaluate the conduction losses use the following equation:

 $V_F = 1.47 + 0.010 I_F$ $P = 1.47 \times I_{F(AV)} + 0.010 I_F^{2}_{(RMS)}$

Figure 1. Low frequency power losses versus average current

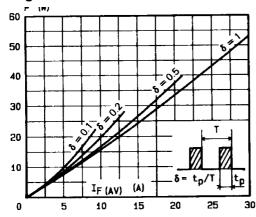


Figure 2. Peak current versus form factor

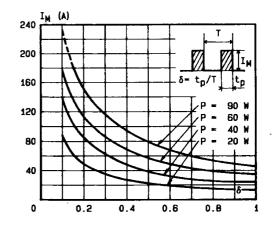


Figure 3. Non repetitive peak surge current versus overload duration

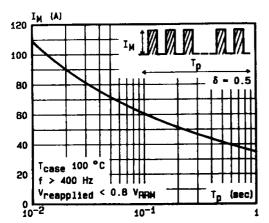


Figure 4. Thermal impedance versus pulse width

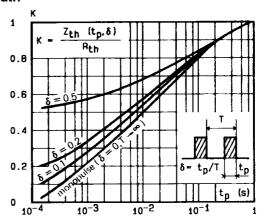


Figure 5. Voltage drop versus forward current

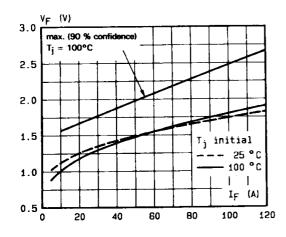


Figure 6. Recovery charge versus di_F/d_t-

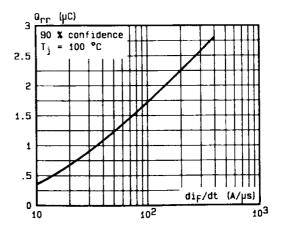


Figure 7. Recovery time versus dif/dt-

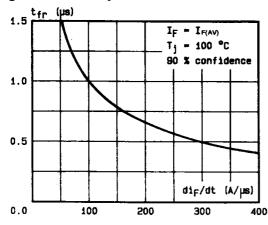


Figure 8. Peak reverse current versus di_F/d_t-

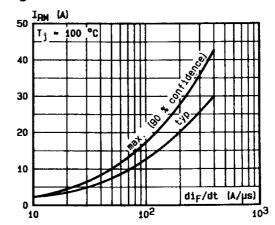


Figure 9. Peak forward voltage versus dir/dt-

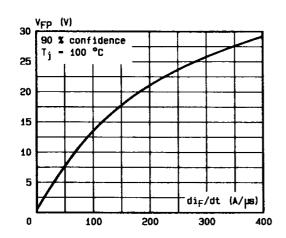


Figure 10. Dynamic parameters versus junction temperature.

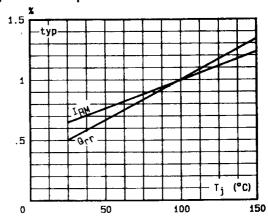


Figure 11. Turn-off switching characteristics (without series inductance).

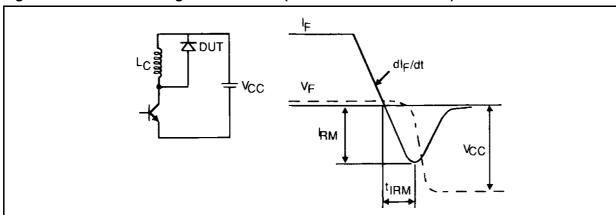
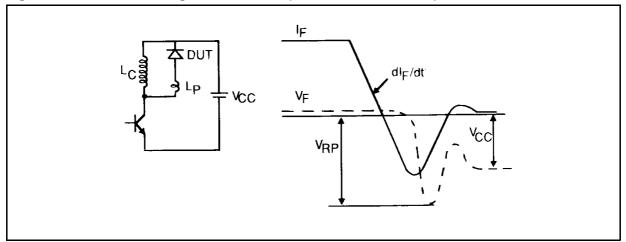


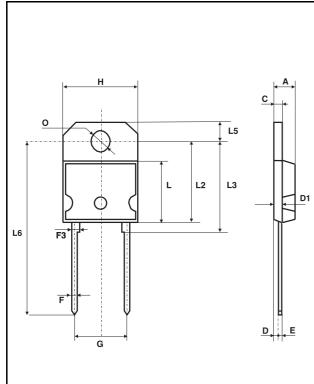
Figure 12. Turn-off switching characteristics (with series inductance)



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PACKAGE MECHANICAL DATA

SOD93 Plastic



	DIMENSIONS							
REF.	Millimeters			Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	4.70		4.90	0.185		0.193		
С	1.17		1.37	0.046		0.054		
D		2.50			0.098			
D1		1.27			0.050			
Е	0.50		0.78	0.020		0.031		
F	1.10		1.30	0.043		0.051		
F3		1.75			0.069			
G	10.80		11.10	0.425		0.437		
Н	14.70		15.20	0.578		0.598		
L			12.20			0.480		
L2			16.20			0.638		
L3		18.0			0.709			
L5	3.95		4.15	0.156		0.163		
L6		31.00			1.220			
0	4.00	_	4.10	0.157		0.161		

Cooling method: by conduction (method C) Marking: type number Recommended torque value: 80cm. N Maximum torque value: 100cm. N

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